

SCI7660C_{0B}/M_{0B}

DC-DC Converter



- 95% Typical Power Efficiency
- Doubled or Output Voltage
- Voltage Conversion (Positive
 ⇔ Negative)

■ DESCRIPTION

The SCI7660CoB/Mob CMOS DC-DC Converter features high operational performance with low power dissipation. The booster generates a doubled output voltage from the input.

It is possible to drive the LSI that need another power supply than main power supply. (LCD drivers•Analog LSI etc.) Its very low power requirement makes it ideal to supply handy equipments with power.

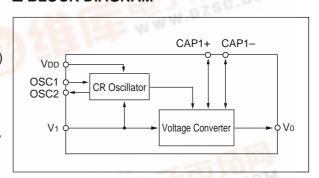
■ FEATURES

- High performance with low power dissipation
- Simple conversion of VDD(-5V) to +VI(+5V), -2VI(-10V)
- Power conversion efficiency 95% Typ.
- Cascade connection

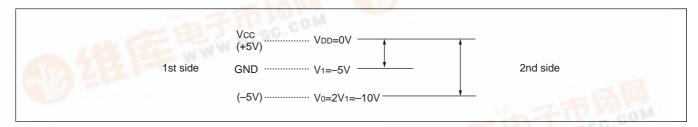
(two device connected VDD = -5V, VO = -15V)

- Low power...... Ideal for dry cell battery
- On-chip CR oscillator

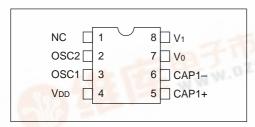
■ BLOCK DIAGRAM



■ VOLTAGE RELATIONS



■ PIN CONFIGURATION



■ PIN DESCRIPTION

Pin Name Pin No.		Function				
OSC1	3	Oscillation register connection terminal				
OSC2	2	Oscillation resister connection terminal				
VDD	4	Power supply terminal (positive, system supply Vcc)				
CAP1+	5	Terminal for connection of capacitor for booster (positive)				
CAP1-	6	Terminal for connection of capacitor for booster (negative)				
Vo	7	Output terminal at doubling				
Vı	8	Power supply terminal (negative, system supply GND)				



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■ ABSOLUTE MAXIMAM RATINGS

 $(Ta = 25^{\circ}C)$

Rating	Symbol	Value	Unit
Input voltage	Vı	-10.0 to 0.5	V
Output voltage	Vo	Min20.0	V
Power dissipation	PD	300 (DIP-8pin) / 150 (SOP4-8pin)	mW
Operating temperature	Topr	-40 to 85	°C
Storage temperature	Tstg	-65 to 150	°C
Soldering temperature and time	Tsol	260°C, 10s (at lead)	_

Note: When this IC is soldered in the solder-reflow process, be sure to maintain the reflow furnace at the curve shown in "Fig. 3-5 Temperature Profile for Standard SMD Package (QFP, SOP, PLCC and etc.) of this DATA BOOK. And this IC can not be exposed to high temperature of the solder dipping.

■ ELECTRICAL CHARACTERISTICS

 $(V_1 = -5V, Ta = -40 \text{ to } 85^{\circ}C)$

Characteristic	Symbol	Condition	Min.	Тур.	Max.	Unit
Input voltage	Vı		-8.0	_	-1.5	V
Output voltage	Vo		-16.0	_	_	V
Booster current consumption	lopr	$RL = \infty$, $ROSC = 1M\Omega$, $VI = -5V$	_	20	30	μΑ
Stationary current	IQ	RL = ∞, VI = -8V	_	_	2.0	μΑ
Output impedamce	Ro	Io = 10mA, VI = -5V	_	75	100	Ω
Booster power conversion efficiency	Peff	Io = 5mA, VI = -5V	90	95	_	%
Input leakage current	ILI	OSC1 terminal, VI = -8V	_	_	2.0	μΑ
Oscillation frequency	fosc	Rosc = $1M\Omega$, VI = $-5V$	16	20	24	kHz

■ RECOMMENDED OPERATING CONDITIONS

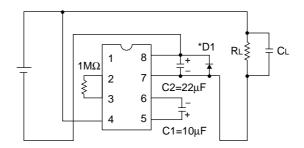
 $(Ta = -40 \text{ to } 85^{\circ}C)$

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Symbol	Remark	Min.	Тур.	Max.	Unit
\/0744	Rosc = $1M\Omega$, $CL/C_2 \le 1/20^{*1}$	_	_	-1.5	V
VSIAT	$C_2 \ge 10 \mu F$ Ta = -20 to $85^{\circ}C$				
VSTA2	$Rosc = 1M\Omega$	_	_	-2.2	V
VSTP	$Rosc = 1M\Omega$	-1.5	_	_	V
RL		RL Min.*2	_	_	Ω
lo		_	_	30	mA
fosc		10	_	30	kHz
Rosc		680	_	2000	kΩ
C1,C2,C3		3.3	_	_	μF
	VSTA1 VSTA2 VSTP RL IO fosc ROSC	$VSTA1 \qquad \begin{array}{c} ROSC = 1M\Omega, \ CL/C2 \leq 1/20^{*1} \\ C2 \geq 10\mu F \ Ta = -20 \ to \ 85^{\circ}C \\ \hline \\ VSTA2 \qquad \qquad ROSC = 1M\Omega \\ \hline \\ VSTP \qquad \qquad ROSC = 1M\Omega \\ \hline \\ RL \qquad \qquad Io \\ \hline \\ fosc \qquad \\ \hline \\ ROSC \qquad \\ \hline \end{array}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Notes: *1: Recommended circuity in low voltage operation is shown below.

^{*2:} RL Min. depends on input voltage as shown below.

Recommended circuit in low voltage operation

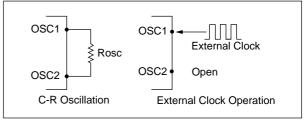


*D1(VF(IF=1mA) \leq 0.6V)

■ CIRCUIT DESCRIPTION

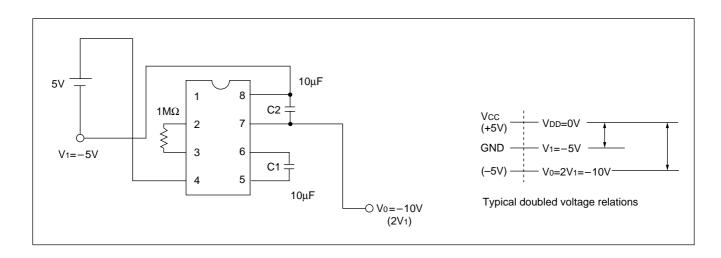
C-R Oscillator

The SCI7660CoB/MoB contains a C-R oscillator for internal oscillation. It consists of an external resistor Rosc connected between the OSC1 pin and OSC2 pin.



Voltage Converters

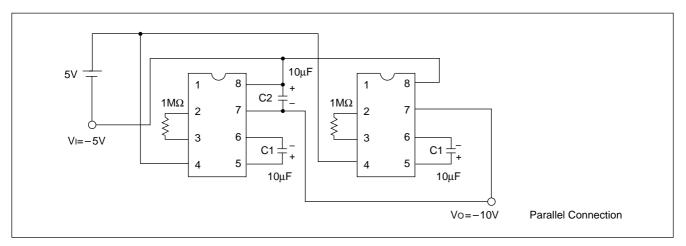
The voltage converters double the input supply voltage (VI) using clocks generated by the C-R oscillator. A doubled voltage can be obtained with a booster capacitor between CAP+ and CAP-, and with a external smoothing capacitor between VI and VO.



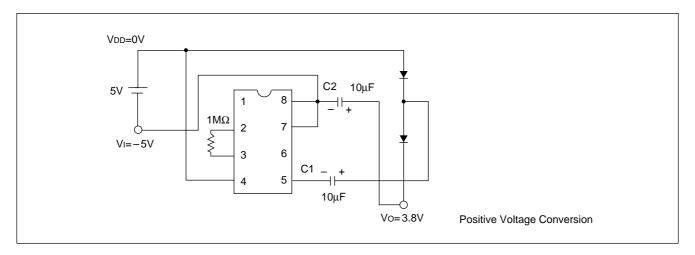
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■ BASIC EXTERNAL CONNECTION

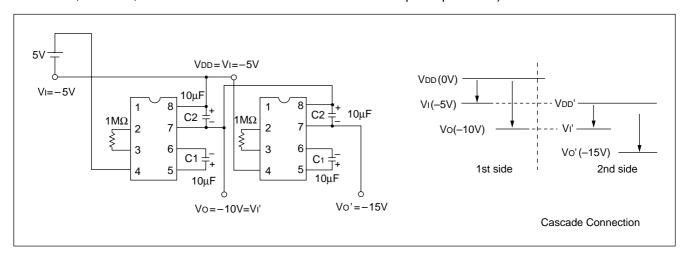
• Parallel Connection (Output impedance can be reduced by parallel connections.)



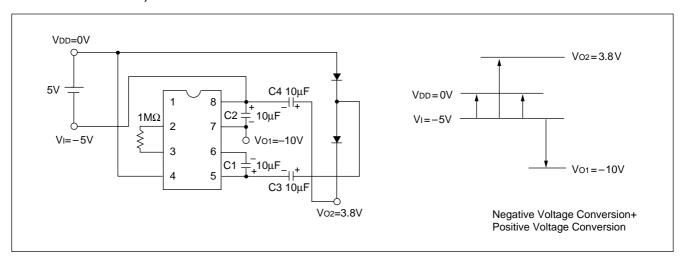
• Positive Voltage Conversion (Input voltage can be doubled toward the positive side with diode.)



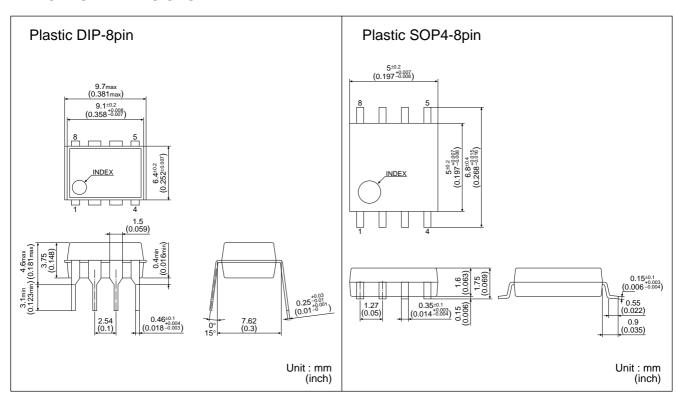
● Cascade Connection (Cascade Connection of SCI7660CoB/MoB further increase the output voltage. Note, however, that the cascade connection increase the output impedance.)



■ Negative Voltage Conversion + Positive Voltage Conversion (This circuit produces outputs of -10V and +3.8V from the -5V input by combination of voltage doubler circuit and positive voltage conversion circuit.)



■ PACKAGE DIMENSIONS



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